

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SA1025, 2SA1081, 2SA1082

Silicon PNP Epitaxial

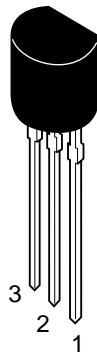
RENESAS

Application

- Low frequency amplifier
- Complementary pair with 2SC2396, 2SC2543 and 2SC2544

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SA1025, 2SA1081, 2SA1082

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	2SA1025	2SA1081	2SA1082	Unit
Collector to base voltage	V_{CBO}	-60	-90	-120	V
Collector to emitter voltage	V_{CEO}	-60	-90	-120	V
Emitter to base voltage	V_{EBO}	-5	-5	-5	V
Collector current	I_C	-100	-100	-100	mA
Emitter current	I_E	100	100	100	mA
Collector power dissipation	P_C	400	400	400	mW
Junction temperature	T_j	150	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	-55 to +150	°C

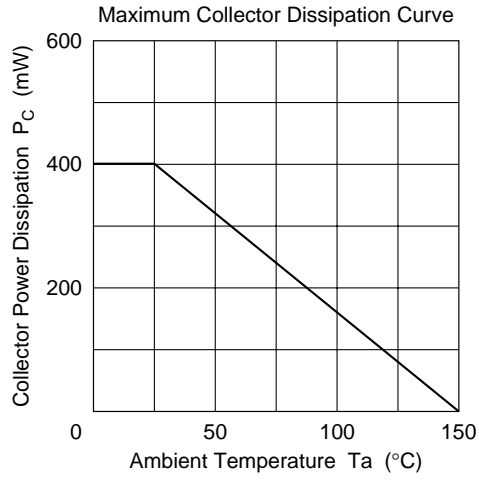
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SA1025			2SA1081			2SA1082			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-60	—	—	-90	—	—	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-60	—	—	-90	—	—	-120	—	—	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	-5	—	—	μA	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-0.1	—	—	-0.1	—	—	-0.1	μA	$V_{CB} = -50 \text{ V}, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	-0.1	—	—	-0.1	—	—	-0.1		$V_{EB} = -2 \text{ V}, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	250	—	800	250	—	800	250	—	800		$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-0.2	—	—	-0.2	—	—	-0.2	V	$I_C = -10 \text{ mA}, I_B = -1 \text{ mA}$
Base to emitter voltage	V_{BE}	—	-0.6	—	—	-0.6	—	—	-0.6	—	V	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Gain bandwidth product	f_T	—	90	—	—	90	—	—	90	—	MHz	$V_{CE} = -12 \text{ V}, I_C = -2 \text{ mA}$
Collector output capacitance	C_{ob}	—	3.5	—	—	3.5	—	—	3.5	—	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: 1. The 2SA1025, 2SA1081 and 2SA1082 are grouped by h_{FE} as follows.

D	E
250 to 500	400 to 800

See characteristic curves of 2SA1083.



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